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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Jono et al., Keiji

Application No.: 09/652,550

Filed: 08/31/00

Group No.: 2811

Examiner: T.F. Tran

For: Methods of Forming an Isolation Trench in a Semiconductor, Methods of Forming an Isolation Trench in a Surface of a Silicon Wafer, Methods of Forming an Isolation Trench-Isolated Transistor, Trench-Isolated Transistor, Trench Isolation Structures Formed in a Semiconductor, Memory Cells and DRAMS

Assistant Commissioner for Patents Washington, D.C. 20231

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